

Title (en)

METHOD FOR THE PRODUCTION OF SONOS MEMORY CELLS

Title (de)

VERFAHREN ZUR HERSTELLUNG VON SONOS-SPEICHERZELLEN

Title (fr)

PROCEDE POUR FABRIQUER DES CELLULES MEMOIRES SONOS

Publication

EP 1535338 A2 20050601 (DE)

Application

EP 03794774 A 20030731

Priority

- DE 0302576 W 20030731
- DE 10240893 A 20020904

Abstract (en)

[origin: WO2004025731A2] Disclosed is an Si body (1) in which a ditch (2) is created, the walls (4) of said ditch (2) being provided with a nitrogen implant (6). An oxide layer which is disposed between the source/drain areas (5) and a word line that is applied to the upper face grows thicker than a lower oxide layer of an ONO storage layer that is created on the ditch wall as a gate dielectric. A metal silicide layer can be created on the upper faces of the source/drain areas instead of the nitrogen implant in the ditch walls in order to accelerate oxide growth there.

IPC 1-7

H01L 27/115; **H01L 21/8246**; **H01L 29/792**; **H01L 21/336**

IPC 8 full level

H01L 21/28 (2006.01); **H01L 21/336** (2006.01); **H01L 29/792** (2006.01); **H10B 20/00** (2023.01); **H10B 69/00** (2023.01)

CPC (source: EP US)

H01L 29/40117 (2019.08 - EP US); **H01L 29/66833** (2013.01 - EP US); **H01L 29/792** (2013.01 - EP US); **H01L 29/7926** (2013.01 - EP US); **H10B 43/30** (2023.02 - EP US); **H10B 69/00** (2023.02 - EP US)

Cited by

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